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48G. Modeling for Variability and Manufacturing	
Session Date:	March 9(Thu.), 2023
Session Time:	16:30-17:55
Session Room:	Room G (#318)
Session Chair	Prof. Jong-Ho Bae (Kookmin University)

[48G-1] [Invited] **16:30-16:55**

Advanced Compact Modeling for Transistor Aging: Trap-Based Approaches and Mixed-Mode Coupling

Runsheng Wang[1], Zixuan Sun[1], Yu Li[1], Yongkang Xue[2], Zirui Wang[1], Pengpeng Ren[2], Zhigang Ji[1,2], Lining Zhang[1] and Ru Huang[1]

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[48G-2] **16:55-17:10**

Integrated Wafer and Die Level Simulation of Back End of Line Chemical Mechanical Polishing Processes

Ushasree Katakamsetty[1], Stefan Nikolaev Voykov[2], Boris Vasilev[3], Sam Nakagawa[4], Tamba Tugbawa[5], Jansen Chee[6], Aaron Gower-Hall[7], Brian Lee[7], Weiyang Zhu[8], Bifeng Li[8] and Kimiko Ichikawa[9]

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[48G-3] **17:10-17:25**

Introduction and Research of All Wafer Intelligent Monitoring (AIM) System

Junho Roh, Jinil Kim, Hong-Goo Lee, Sang-Ho Lee and Jaewook Seo

SK hynix Inc.

[48G-4] **17:25-17:40**

Drain Current Variability in 2-Levels Stacked Nanowire Gate All Around P-Type Field Effect Transistors

Donghyun Kim[1,2], Sylvain Barraud[3], Gerard Ghibaudo[1], Christoforos Theodorou[1] and Jae Woo Lee[2]

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[48G-5] **17:40-17:55**

Application of Deep Artificial Neural Network to Model Characteristic Fluctuation of Multi-Channel Gate-All-Around Silicon Nanosheet and Nanofin MOSFETs Induced by Random Nanosized Metal Grains

Sagarika Dash, Yiming Li and Wen-Li Sung

National Yang Ming Chiao Tung University